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AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0016] with the following amended paragraph:

[0016] Figure 1A illustrates a top-down view of a surface of a continuous pinned layer 100 to be shared by multiple cells of an MRAM device. The continuous pinned layer 100 may comprise several layers and may be formed using a wide variety of well-known materials and methods. For example, the continuous pinned layer 100 may comprise a vertically stacked set of sublayers including a tantalum seed sublayer, a nickel-iron seed sublayer, a magnesium oxide, ~~iridium-manganese~~ iridium-manganese, platinum-manganese or ~~nickel-manganese~~ nickel-manganese pinning sublayer, and a nickel-iron, nickel-iron-cobalt, cobalt-iron or nickel-iron-chromium sublayer.